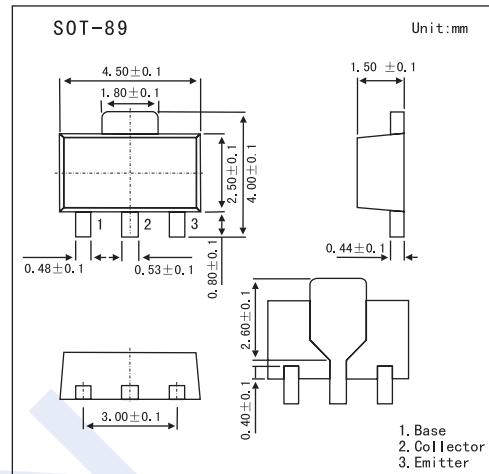# Surface Mount PNP Switching Transistor
CXT2907A

■ Features

● High current (max.600mA)

● Low voltage (max.60V)

SOT-89 package dimensions (Unit:mm)

1. Base
2. Collector
3. Emitter

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-60	V
Collector-emitter voltage	V_{CEO}	-60	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current (DC)	I_C	-600	mA
Power dissipation	P_D	1.2	W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-65 to +150	℃
Thermal Resistance	$è_{JA}$	104	℃/W

CXT2907A

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base cut-off current	I_{CBO}	$I_E = 0$; $V_{CB} = -50$ V			-10	nA
		$I_E = 0$; $V_{CB} = -50$ V; $T_j = 125$ ℃			-10	μ A
Emitter-base cut-off current	I_{EBO}	$I_C = 0$; $V_{EB} = -5$ V			-50	nA
DC current gain	h_{FE}	$I_C = -0.1$ mA; $V_{CE} = -10$ V	75			
		$I_C = -1$ mA; $V_{CE} = -10$ V	100			
		$I_C = -10$ mA; $V_{CE} = -10$ V	100			
		$I_C = -150$ mA; $V_{CE} = -10$ V	100		300	
		$I_C = -500$ mA; $V_{CE} = -10$ V	50			
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -150$ mA; $I_B = -15$mA			-0.4	V
		$I_C = -500$ mA; $I_B = -50$ mA			-1.6	V
Base-emitter saturation voltage	V_{BEsat}	$I_C = -150$ mA; $I_B = -15$ mA			-1.3	V
		$I_C = -500$ mA; $I_B = -50$ mA			-2.6	V
Turn-on time	t_{on}	V_{CC}=30V, V_{BE}=-0.5V,I_C=-150mA, I_{B1}=-15mA			45	ns
Delay time	t_d				10	ns
Rise time	t_r				40	ns
Turn-off time	t_{off}	V_{CC}=-6.0V,I_C=-150mA, I_{B1}=I_{B2}=-15mA			100	ns
Storage time	t_s				80	ns
Fall time	t_f				30	ns
Transition frequency	f_T	$I_C = -50$ mA; $V_{CE} = -20$ V; f = 100 MHz	200			MHz

■ Marking

Marking	2907A

CXT2907A

Typical Characteristics

Typical Pulsed Current Gain vs Collector Current

Collector-Emitter Saturation Voltage vs Collector Current

Base-Emitter Saturation Voltage vs Collector Current

Base Emitter ON Voltage vs Collector Current

Collector-Cutoff Current vs Ambient Temperature

Input and Output Capacitance vs Reverse Bias Voltage